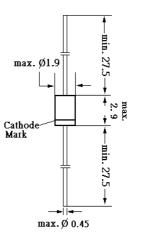
SILICON EPITAXIAL PLANAR DIODE Fast switching diode



Glass case JEDEC DO-34 Dimensions in mm

Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit			
Reverse Voltage	V _R	50	V			
Peak Reverse Voltage	V _{RM}	60	V			
Rectified Current (Average)						
Half Wave Rectification with Resist. Load	Ι _ο	130 ¹⁾	mA			
at T_{amb} = 25°C and f/50 H _Z						
Surge Forward Current at t<1s and $T_j = 25^{\circ}C$	I _{FSM}	500	mA			
Power Dissipation	P _{tot}	400 ¹⁾	mW			
Junction Temperature	Tj	200	°C			
Storage Temperature Range	Ts	-65 to +200	°C			
¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.						

Characteristics at T_j = 25°C

	Symbol	Min.	Тур.	Max.	Unit	
Forward Voltage at I _F = 100mA	V _F	-	-	1.1	V	
Leakage Current at V _R = 50V	I _R	-	-	0.5	μA	
Reverse Breakdown Voltage tested with 100µA Pulses	V _{(BR)R}	60	-	-	V	
Capacitance at $V_F = V_R = 0$	C _{tot}	-	-	3	pF	
Reverse Recovery Time from I_F = 10mA to I_R = 1mA, V_R = 6V, R_L = 100 Ω	t _{rr}	-	-	4	ns	
¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.						



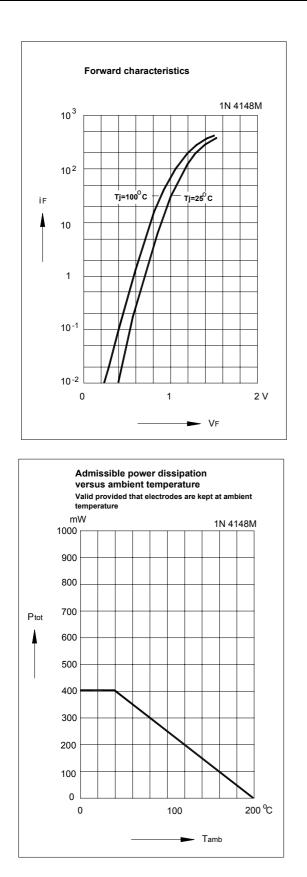
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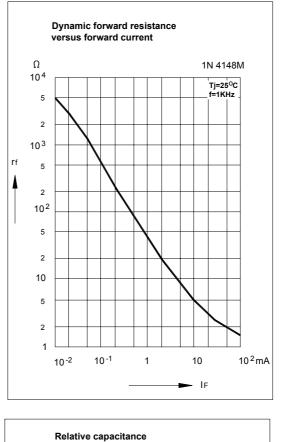


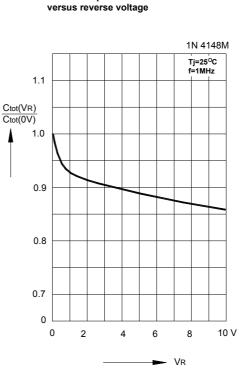




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Dated : 31/12/2002